NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLW32** is Designed for Television Band IV & V Applications up to 860 MHz.

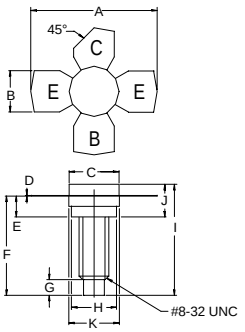
FEATURES:

- Common Emitter
- P_G = 11 dB at 0.5 W/ 860 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	1.0 A
V_{CBO}	50 V
V_{CEO}	30 V
V_{EBO}	4.0 V
P_{DISS}	10.8 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	16 °C/W

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 /5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

ORDER CODE: ASI10677

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I_C = 2.0 mA	50			V
BV_{CEO}	I_C = 15 mA	30			V
BV_{EBO}	I_E = 1.0 mA	4.0			V
I_{CES}	V_{CE} = 30 V			0.5	mA
h_{FE}	V_{CE} = 25 V I_C = 150 mA	20		120	---
P_G	V_{CE} = 25 V I_C = 150 mA f = 860 MHz	11			dB
IMD_1	P_{OUT} = 0.5 W	-60			dBc